SILICON SCHOTTKY BARRIER DIODE

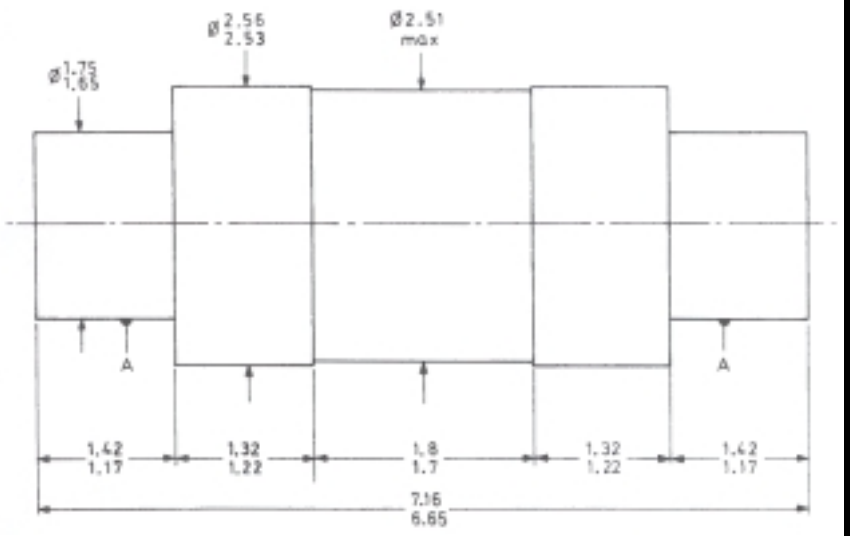
DESCRIPTION:

The **ASI BAT38** is a silicon Schottky barrier mixer diode, Designed for use in Ka frequency band Applications.

FEATURES INCLUDE:

- Low R_S—5.0Ω
- Low NF 8.5 Db Typ.
- Frequency Range 26 to 40 GHz
- Available as Matched pairs by adding the MP to the part number. Matching criteria is ± 10% on rectified current and within 150 Ω i.f. impedance.

PACKAGE STYLE



MAXIMUM RATINGS

V_R	2.0 V
P_{DISS}	250 mW @ T_C = 25 °C
T_J	-55 °C to +100 °C
T_{STG}	-55 °C to +100 °C

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIM	UNITS
V_R	I_R = 10 µA		2.0			V
V_F	I_F = 1.0 mA				0.29	V
I_F	V_F = 0.5 V		2.0			mA
I_R	V_R = 0.5 V				2.0	µA
C_T	V_R = 0 V	f = 1.0 MHz		.27		pF
NF	I_F = 0.5 mA	f = 30 GHz		6.0		dB